

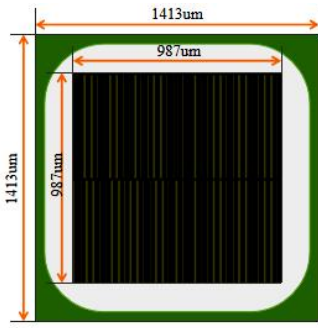
**High Voltage Trench Schottky Diode****FEATURES**

- Trench MOS Schottky technology
- Die in 6" Wafer Form
- 100V, 5A\*
- $V_F=0.70V$ (typ.)\*\*

**Electrical Characteristics** ( $T_j=25^\circ C$ )

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{RRM}$	Maximum repetitive peak reverse voltage	108	118	—	V	$I_R=500\mu A$
$V_F$	Static Forward Voltage	—	0.45	0.48	V	$I_F=1A$
		—	0.58	0.65	V	$I_F=3A$
		—	0.70	0.73	V	$I_F=5A$
$I_R^{***}$	Cathode-To-Anode Leakage Current	—	3	20	$\mu A$	$V_R=100V$
$T_j, T_{STG}$	Operating and Storage Temperature Range	-55°C to 150°C Max				
*** Pulse width < 300 uS, Duty cycle < 2%						

**Mechanical Data**

Die Size	1473×1473	$\mu m^2$	<b>CHIP DRAWING</b> (Scribe Line is Excluded) 
Source Pad Size	987×987	$\mu m^2$	
Scribe Line Size	60	$\mu m$	
Wafer Diameter	6	in	
Wafer Thickness	250	$\mu m$	
Estimated Gross Die	7321 (Yield>98%)		
Anode Metal Thickness	Al\Ti\Ni\Ag(2.8um\0.1um\0.2um\1.8um)		
Cathode Metal Thickness	Ti\Ni\Ag(0.2um\0.3um\2um)		
Recommended Storage Environment	Store in original container, in dry nitrogen, < 6 months at an ambient temperature of 23°C±3°C >		

\* Electrical characteristics are reported for the reference packaged part (TO-220) and can not be guaranteed in die sales form.

\*\* Electrical characteristics are reported for the bare die. Variations in customer packaging materials, dimensions and processes may affect parametric performance.